

OptiMOS®-P Small-Signal-Transistor Feature

- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101

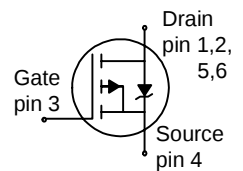
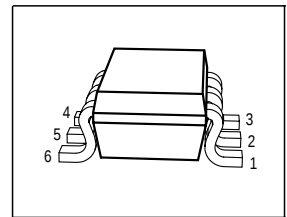


Type	Package	Tape and reel	Marking
BSL211SP	P-TSOP6-6	L6327: 3000pcs/r.	sPB

Product Summary

V_{DS}	-20	V
$R_{DS(on)}$	67	mΩ
I_D	-4.7	A

P-TSOP6-6



Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	I_D	-4.7 -3.8	A
Pulsed drain current $T_A=25^\circ\text{C}$	$I_{D \text{ puls}}$	-18.8	
Avalanche energy, single pulse $I_D=-4.7 \text{ A}$, $V_{DD}=-10\text{V}$, $R_{GS}=25\Omega$	E_{AS}	26	mJ
Reverse diode dv/dt $I_S=-4.7\text{A}$, $V_{DS}=-16\text{V}$, $di/dt=200\text{A}/\mu\text{s}$, $T_{j\text{max}}=150^\circ\text{C}$	dv/dt	-6	kV/ μs
Gate source voltage	V_{GS}	± 12	V
Power dissipation $T_A=25^\circ\text{C}$	P_{tot}	2	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESD22-A114-HBM		Class 0	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	50	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	230	
@ 6 cm ² cooling area ¹⁾		-	-	62.5	

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=-250\mu A$	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-25\mu A$	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current $V_{DS}=-20V, V_{GS}=0, T_j=25^{\circ}C$ $V_{DS}=-20V, V_{GS}=0, T_j=150^{\circ}C$	I_{DSS}	- -	-0.1 -10	-1 -100	μA
Gate-source leakage current $V_{GS}=-12V, V_{DS}=0$	I_{GSS}	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-2.5V, I_D=-3.7A$	$R_{DS(on)}$	-	94	110	m Ω
Drain-source on-state resistance $V_{GS}=-4.5, I_D=-4.7A$	$R_{DS(on)}$	-	54	67	

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air; $t \leq 5$ sec.

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$ V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ $I_D = -3.8\text{A}$	6.2	12.4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0, V_{DS} = -15\text{V},$ $f = 1\text{MHz}$	-	654	-	pF
Output capacitance	C_{oss}		-	241	-	
Reverse transfer capacitance	C_{rss}		-	197	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V},$ $I_D = -1\text{A}, R_G = 6\Omega$	-	8.7	13	ns
Rise time	t_r		-	13.9	21	
Turn-off delay time	$t_{d(off)}$		-	25	37.3	
Fall time	t_f		-	23.3	35	

Gate Charge Characteristics

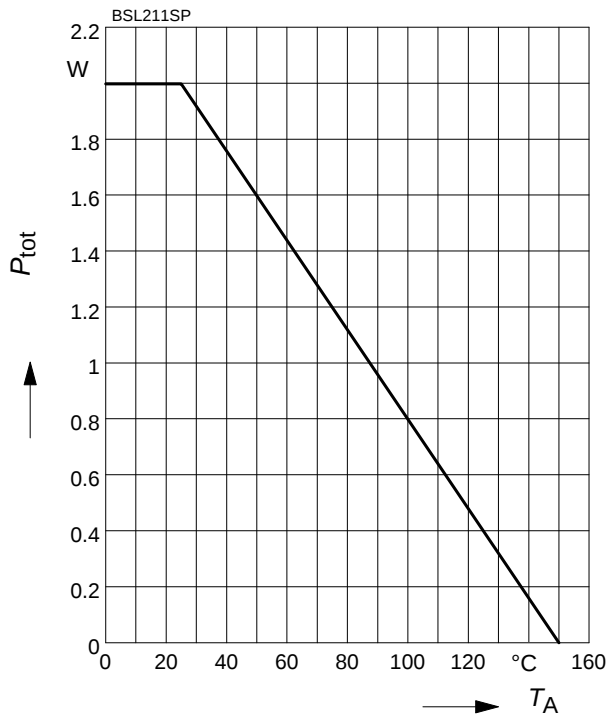
Gate to source charge	Q_{gs}	$V_{DD} = -10\text{V}, I_D = -4.7\text{A}$	-	-1.3	-2	nC
Gate to drain charge	Q_{gd}		-	-4.7	-7	
Gate charge total	Q_g	$V_{DD} = -10\text{V}, I_D = -4.7\text{A},$ $V_{GS} = 0 \text{ to } -4.5\text{V}$	-	-8.3	-12.4	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -10\text{V}, I_D = -4.7\text{A}$	-	-2	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25^\circ\text{C}$	-	-	-2	A
Inverse diode direct current, pulsed	I_{SM}		-	-	-18.8	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0, I_F = I_D $	-	-0.94	-1.4	V
Reverse recovery time	t_{rr}	$V_R = -10\text{V}, I_F = I_D ,$ $di_F/dt = 100\text{A}/\mu\text{s}$	-	20.6	25.8	ns
Reverse recovery charge	Q_{rr}		-	6.3	7.9	

1 Power dissipation

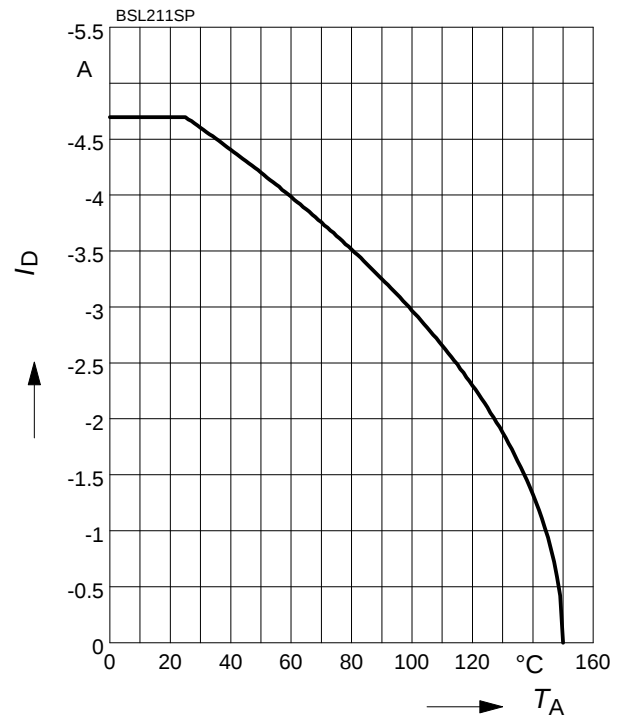
$$P_{\text{tot}} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

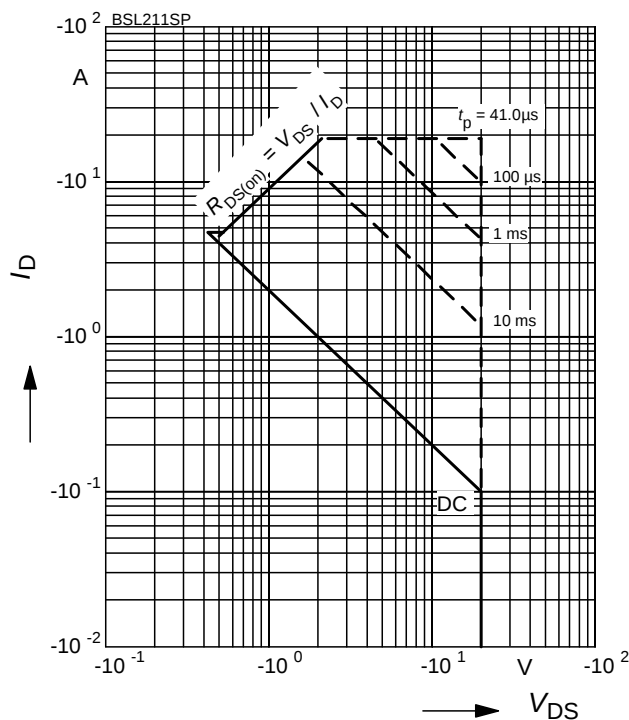
parameter: $|V_{GS}| \geq 4.5 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

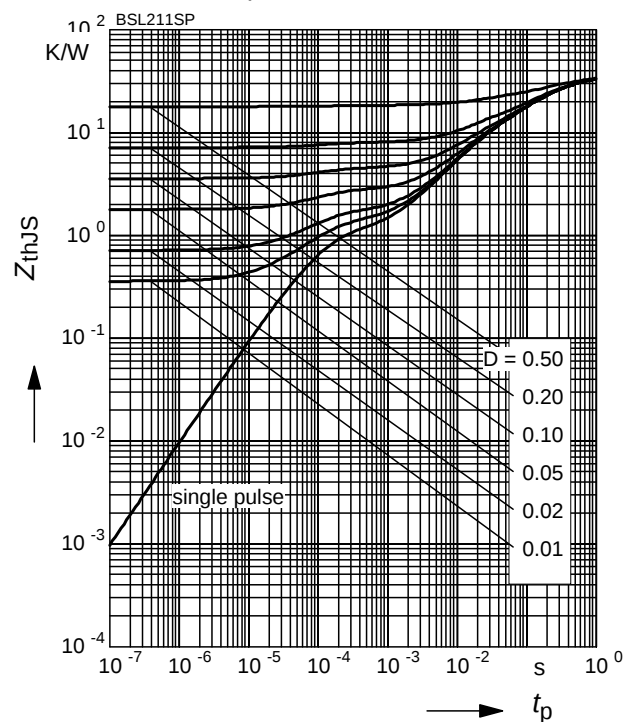
parameter: $D = 0$, $T_A = 25 \text{ °C}$



4 Transient thermal impedance

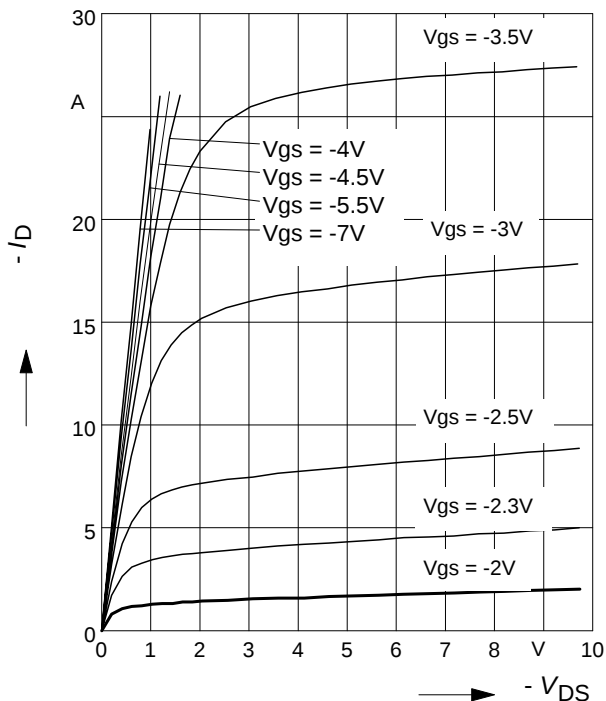
$$Z_{\text{thJS}} = f(t_p)$$

parameter: $D = t_p/T$



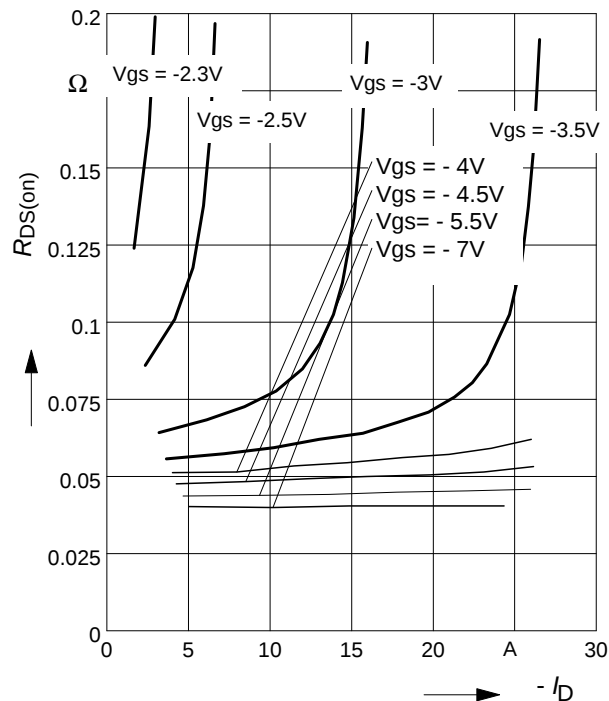
5 Typ. output characteristic

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: $t_p = 80 \mu\text{s}$


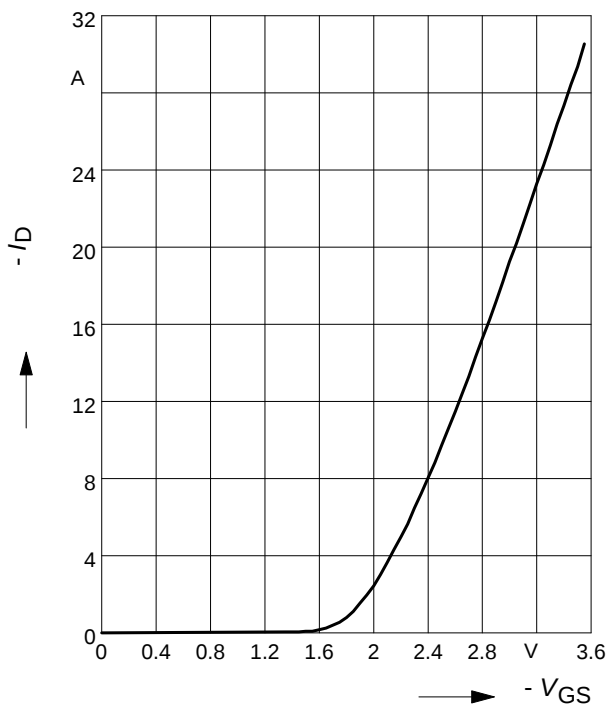
6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D)$

parameter: V_{GS}


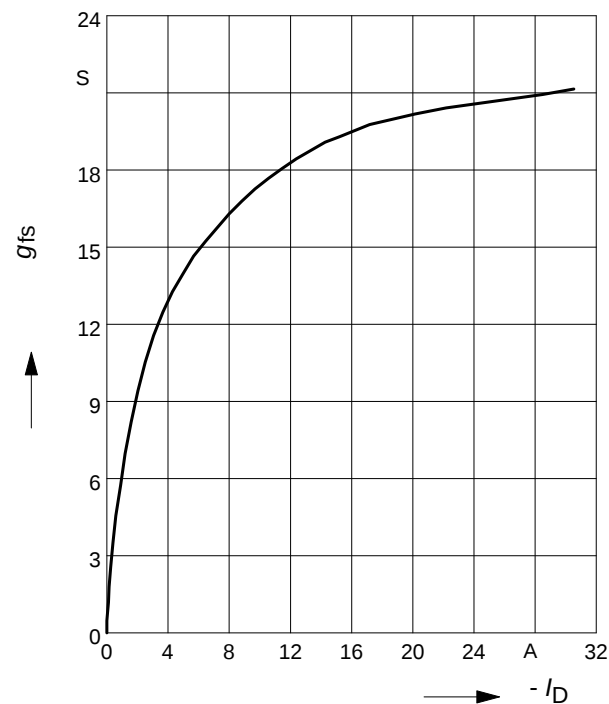
7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

parameter: $t_p = 80 \mu\text{s}$


8 Typ. forward transconductance

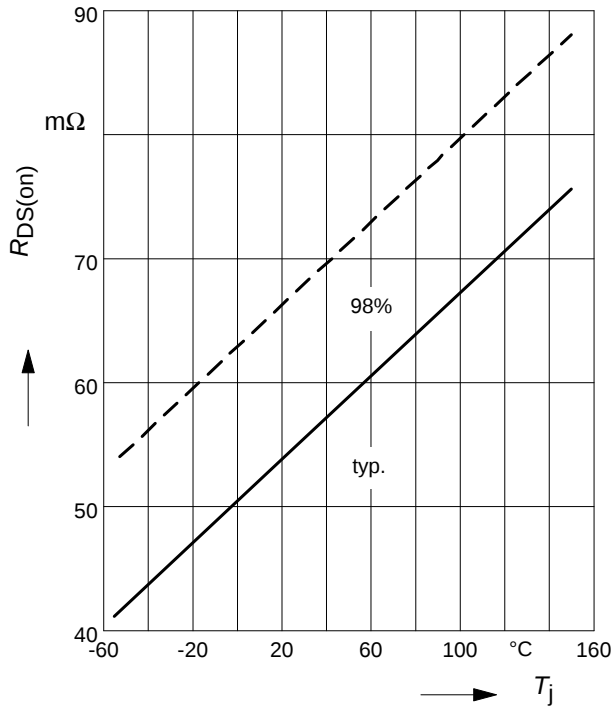
 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

parameter: $t_p = 80 \mu\text{s}$


9 Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

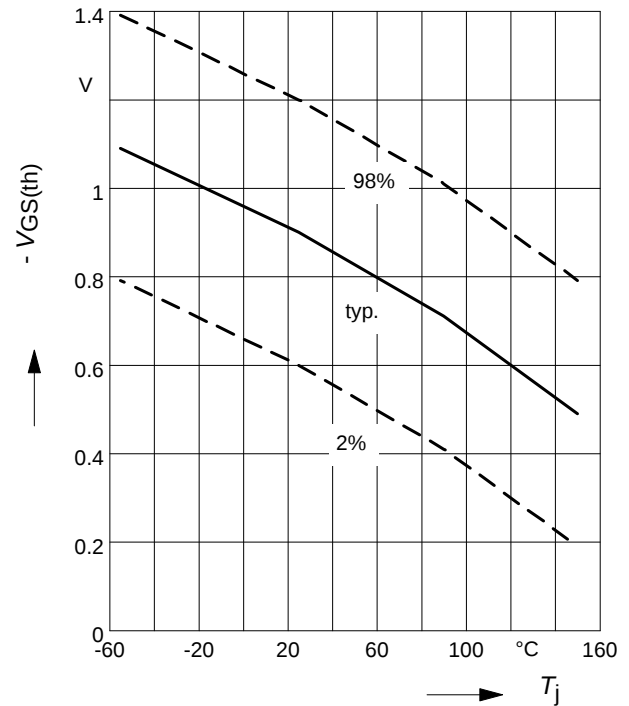
parameter: $I_D = -4.7 \text{ A}$, $V_{GS} = -4.5 \text{ V}$



10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

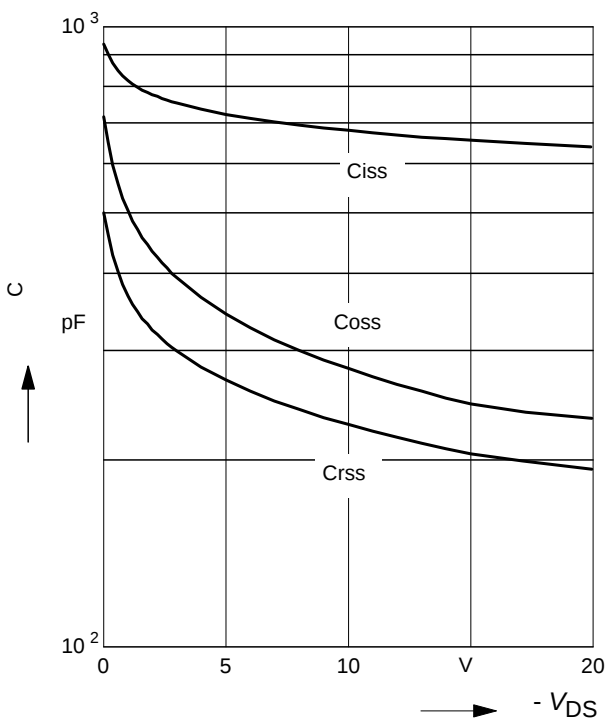
parameter: $V_{GS} = V_{DS}$, $I_D = -25 \mu\text{A}$



11 Typ. capacitances

$$C = f(V_{DS})$$

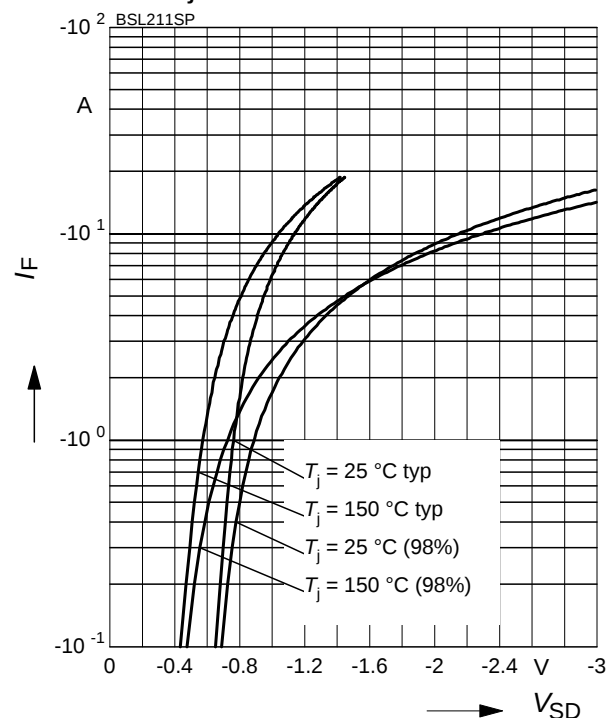
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$



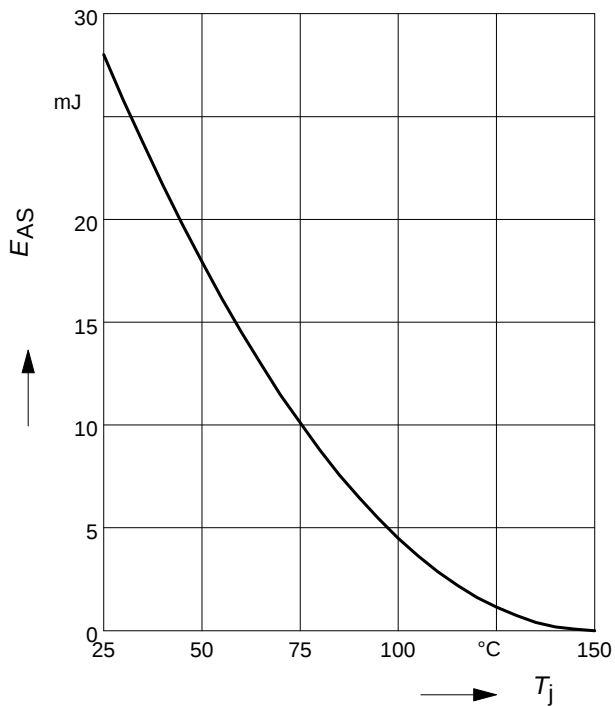
12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

parameter: T_j , $t_p = 80 \mu\text{s}$

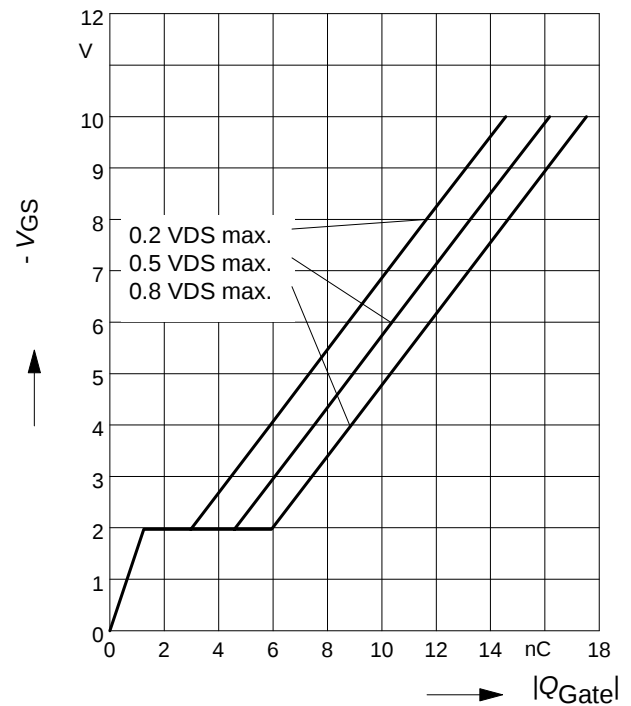


13 Typ. avalanche energy

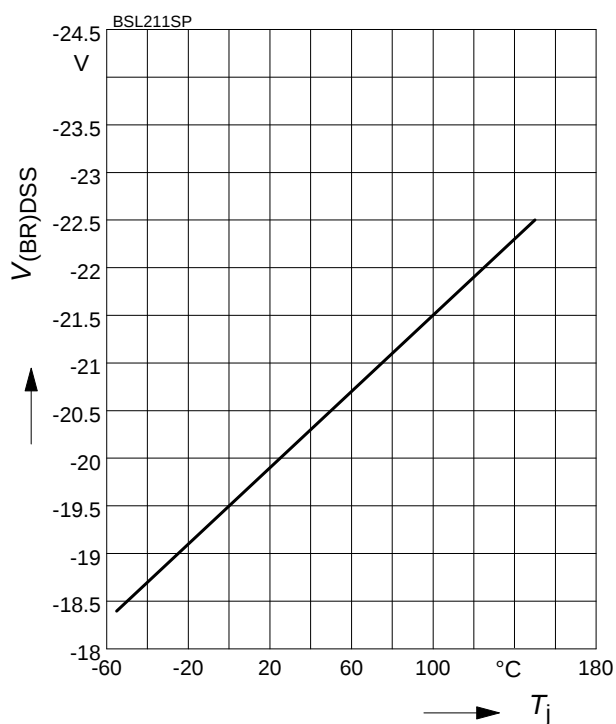
 $E_{AS} = f(T_j)$, par.: $I_D = -4.7\text{ A}$
 $V_{DD} = -10\text{ V}$, $R_{GS} = 25\ \Omega$


14 Typ. gate charge

 $|V_{GS}| = f(Q_{Gate})$

parameter: $I_D = -4.7\text{ A}$ pulsed


15 Drain-source breakdown voltage

 $V_{(BR)DSS} = f(T_j)$


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